

ABSTRACT

Provides an IC chip for high frequency region,
particularly, packaged substrate in which no malfunction or
5 error occurs even if 3 GHz is exceeded.

A conductive layer 34P is formed in the thickness of 30 μ m on
a core substrate 30 and a conductive circuit 58 on an interlayer
resin insulation layer 50 is formed in the thickness of 15 μ m.
By thickening the conductive layer 34P, the volume of the
10 conductor itself can be increased thereby decreasing its
resistance. Further, by using the conductive layer 34 as a
power source layer, the capacity of supply of power to an IC
chip can be improved.

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